

TVS Diode

Transient Voltage Suppressor Diodes

ESD5V3L1B Series

Bi-directional Low Capacitance ESD / Transient Protection Diode

ESD5V3L1B-02LRH
ESD5V3L1B-02LS

Data Sheet

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Final

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Revision History

Page or Item	Subjects (major changes since previous revision)
Revision 1, 2011-08-04	
8	Figure 3-1 have been updated.
Revision 1.0, 2011-05-04	

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Last Trademarks Update 2010-10-26

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1 Bi-directional Low Capacitance ESD / Transient Protection Diode

1.1 Features

- ESD / transient protection of signal lines in low voltage applications according to:
 - IEC61000-4-2 (ESD): ± 20 kV (air / contact)
 - IEC61000-4-4 (EFT): 40 A (5/50 ns)
- Bi-directional, symmetrical working voltage up to $V_{RWM} = \pm 5.3$ V
- Low capacitance: $C_L = 5$ pF (typical)
- Low clamping voltage, low dynamic resistance down to: $R_{DYN} = 0.22 \Omega$ (typical)
- Pb-free (RoHS compliant) and halogen free package, very small form factor: $0.62 \times 0.32 \times 0.31$ mm³



1.2 Application Examples

- Keypad, touchpad, buttons, convenience keys
- LCD displays, Camera, audio lines, mobile communication, Consumer products (E-Book, MP3, DVD, DSC...)
- Notebooks tablets and desktop computers and their peripherals

2 Product Description

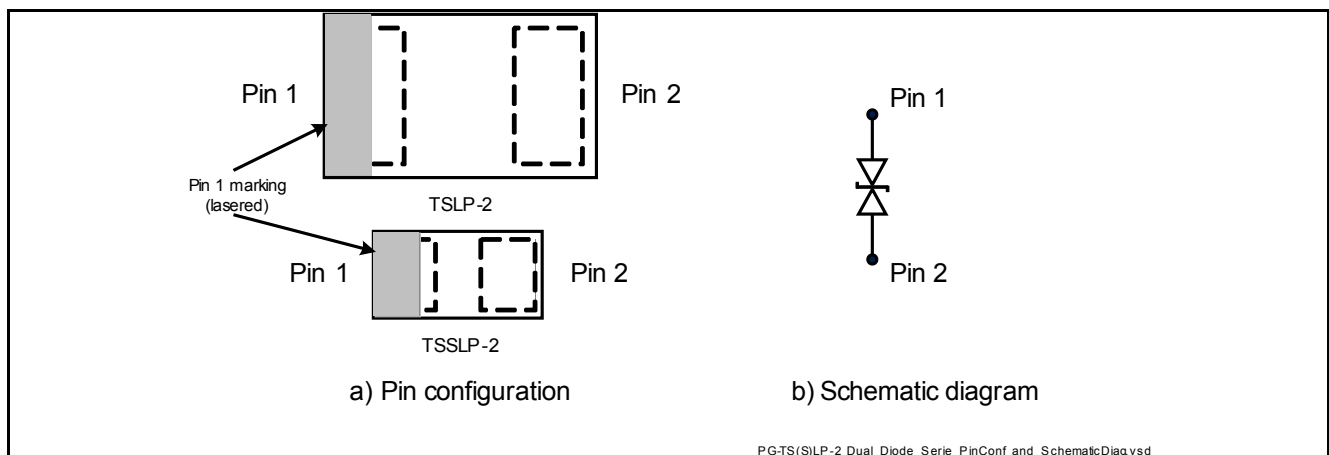


Figure 2-1 Pin Configuration and Schematic Diagram

Table 2-1 Ordering Information

Type	Package	Configuration	Marking code
ESD5V3L1B-02LRH	PG-TSLP-2-17	1 line, bi-directional	4
ESD5V3L1B-02LS	PG-TSSLP-2-1	1 line, bi-directional	C

3 Characteristics

Table 3-1 Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
ESD contact discharge ¹⁾	V_{ESD}	–	–	20	kV
Operating temperature range	T_{OP}	-40	–	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-65	–	150	$^\circ\text{C}$

1) V_{ESD} according to IEC61000-4-2

3.1 Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

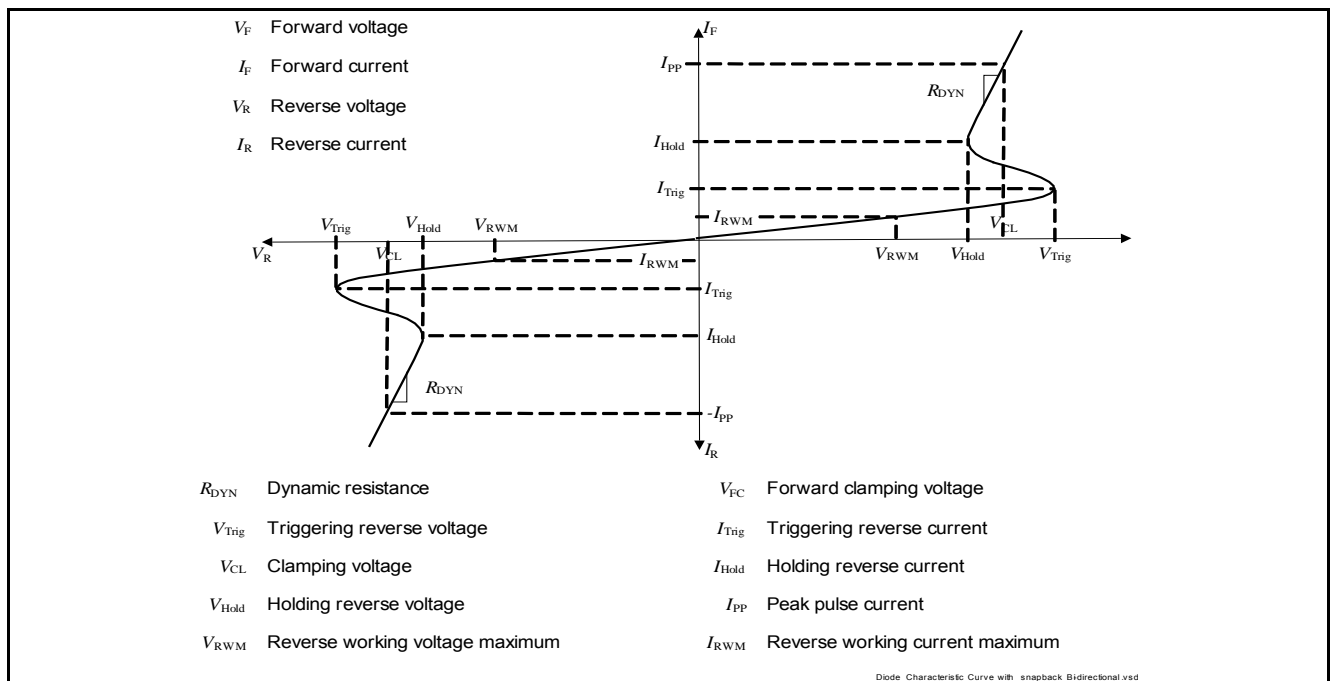


Figure 3-1 Definitions of electrical characteristics

Table 3-2 DC Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	-5.3	–	5.3	V	
Breakdown voltage	V_{BR}	6	–	10	V	$I_{BR} = 1\text{ mA}$
Reverse current	I_R	–	–	100	nA	$V_R = 5.3\text{ V}$

Characteristics
Table 3-3 RF Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Line capacitance	C_L	4	–	7	pF	$V_R = 0\text{ V}, f = 1\text{ MHz}$
Serie inductance	L_S	–	0.4	–	nH	PG-TSLP-2-17
			0.2			PG-TSSLP-2-1

Table 3-4 ESD Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clamping voltage ¹⁾	V_{CL}	–	10.2	–	V	$I_{PP} = 16\text{ A}$, from Pin 1 to Pin 2
		–	13.2	–	V	$I_{PP} = 30\text{ A}$, from Pin 1 to Pin 2
		–	12.1	–		$I_{PP} = 16\text{ A}$, from Pin 2 to Pin 1
		–	17.2	–		$I_{PP} = 30\text{ A}$, from Pin 2 to Pin 1
Dynamic resistance ¹⁾	R_{DYN}	–	0.22	–	Ω	Pin 1 to Pin 2
		–	0.37	–	Ω	Pin 2 to Pin 1

1) Please refer to Application Note AN210 [1]. TLP parameter: $Z_0 = 50\ \Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristics between $I_{PP1} = 10\text{ A}$ and $I_{PP2} = 40\text{ A}$.

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

4 Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

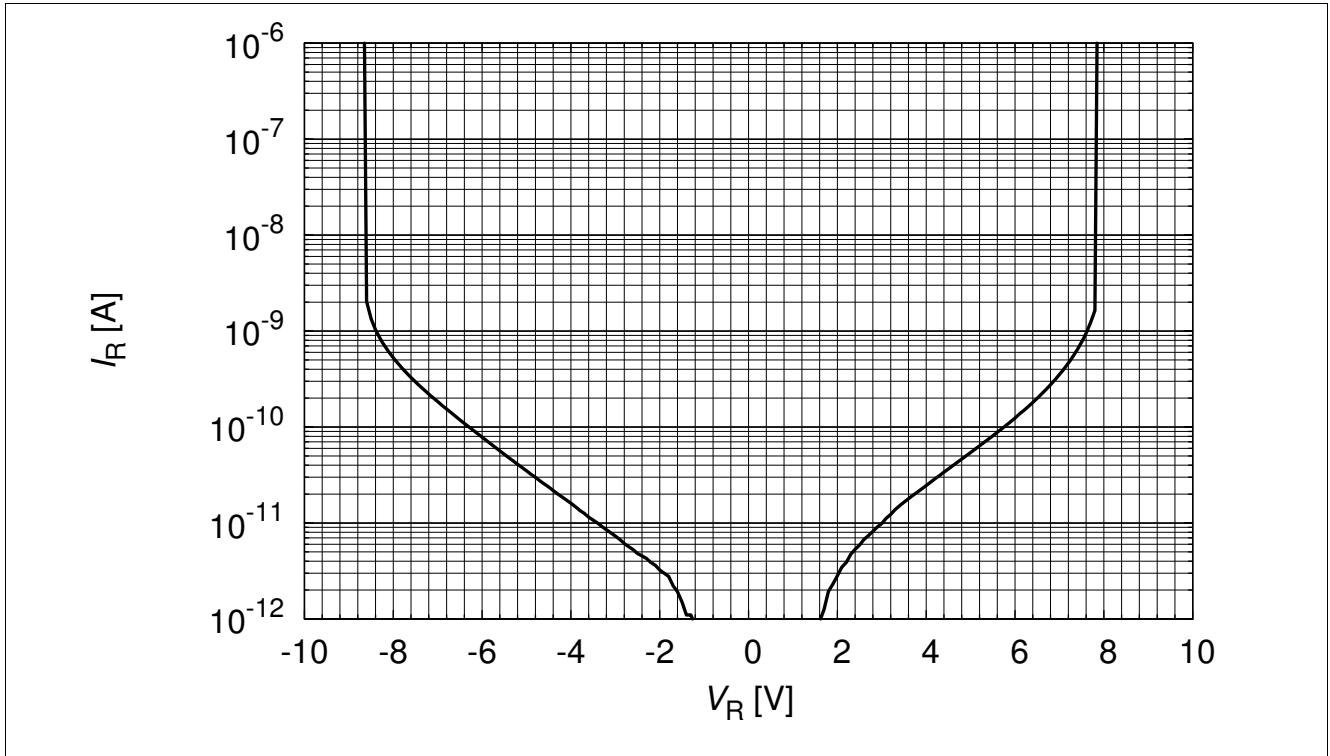


Figure 4-1 Reverse current: $I_R = f(V_R)$

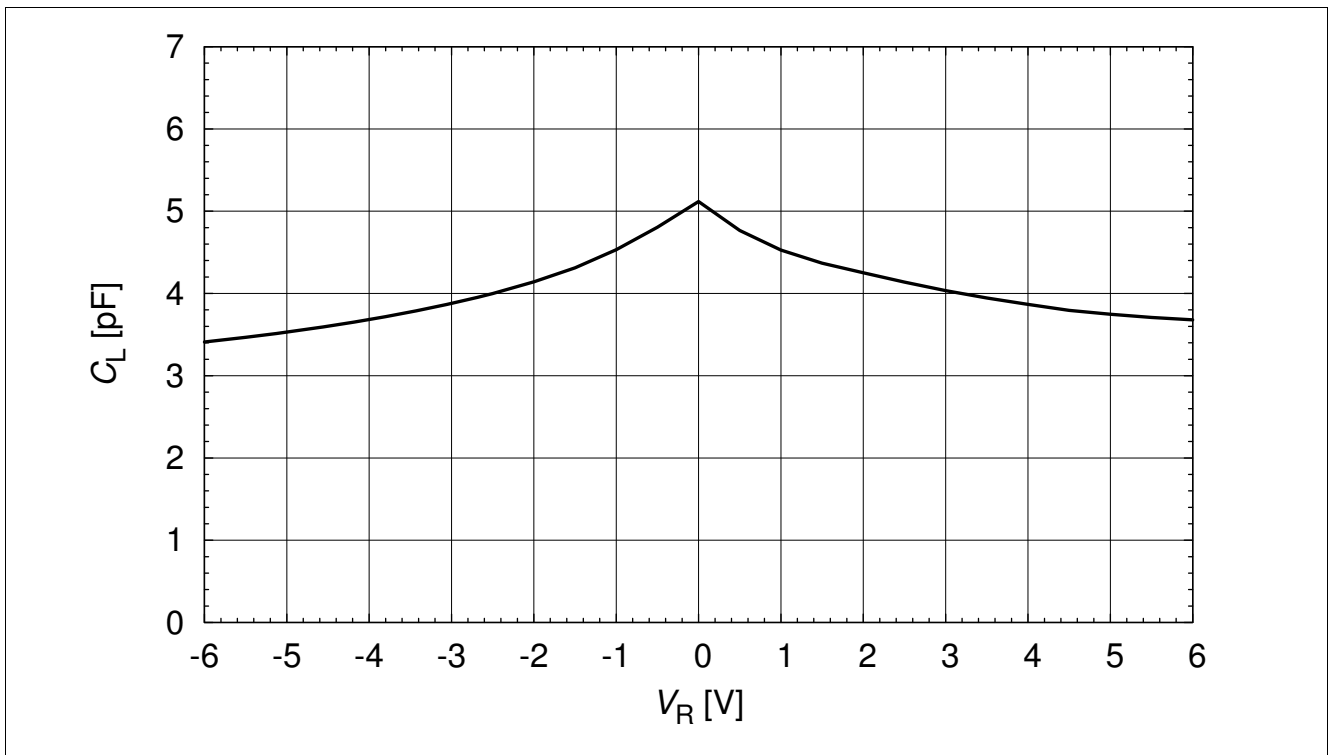


Figure 4-2 Line capacitance: $C_L = f(V_R), f = 1\text{ MHz}$

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

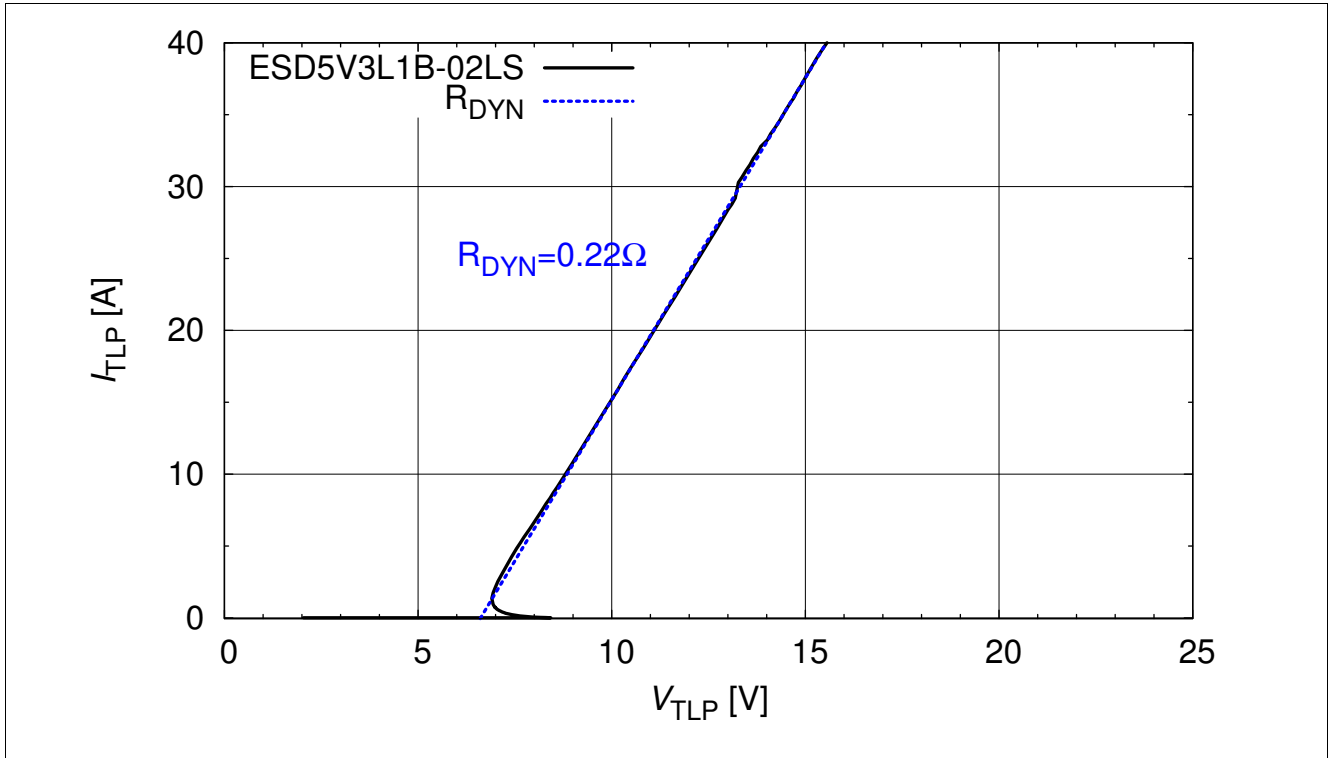


Figure 4-3 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$, from pin 1 to pin 2 [1]

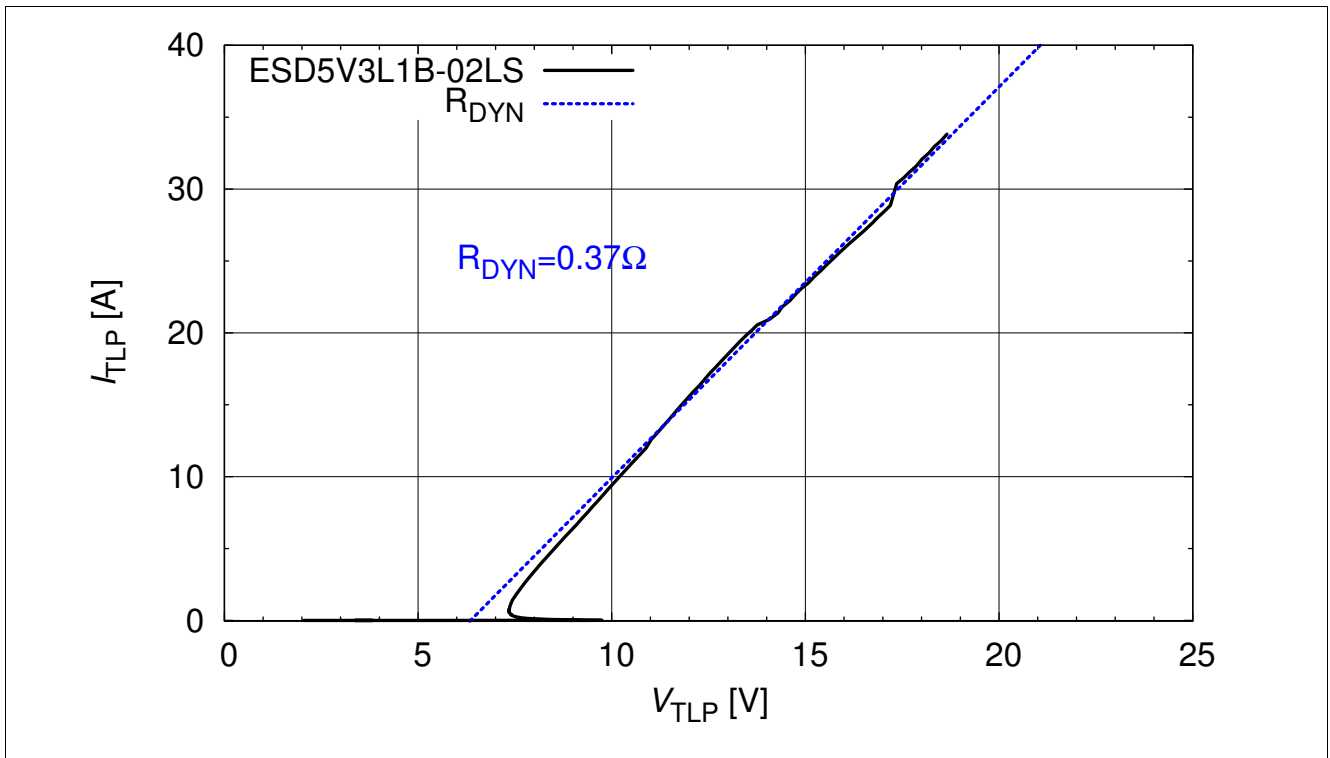


Figure 4-4 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$, from pin 2 to pin 1 [1]

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

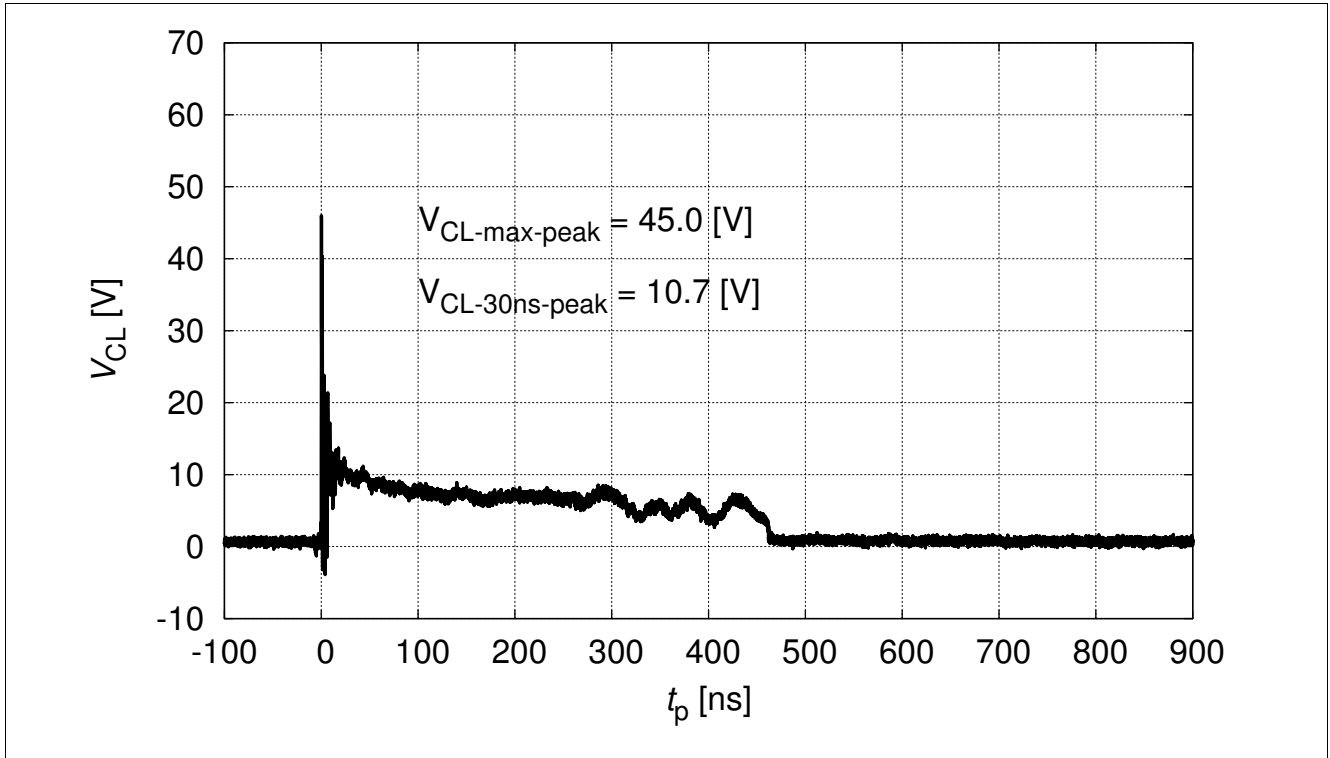


Figure 4-5 IEC61000-4-2 : $V_{CL} = f(t)$, 8 kV positive pulse from pin 1 to pin 2

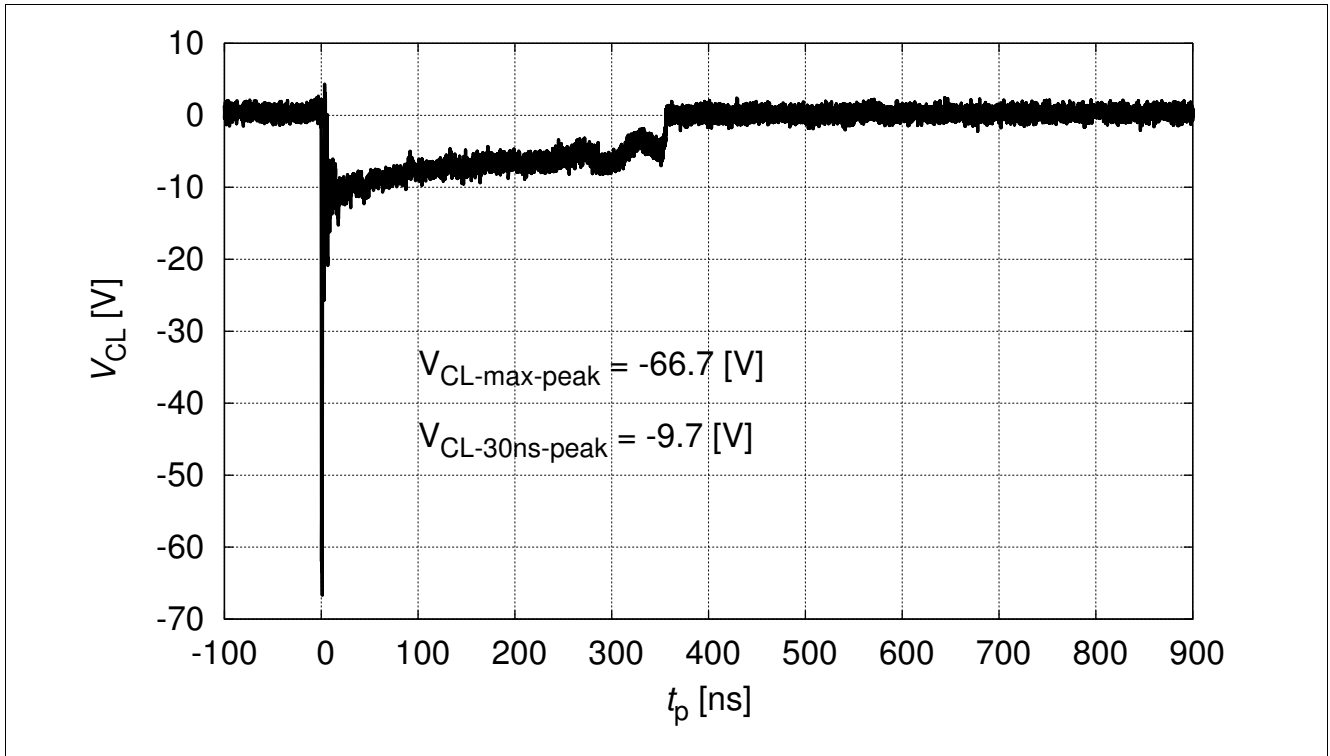


Figure 4-6 IEC61000-4-2 : $V_{CL} = f(t)$, 8 kV negative pulse from pin 1 to pin 2

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

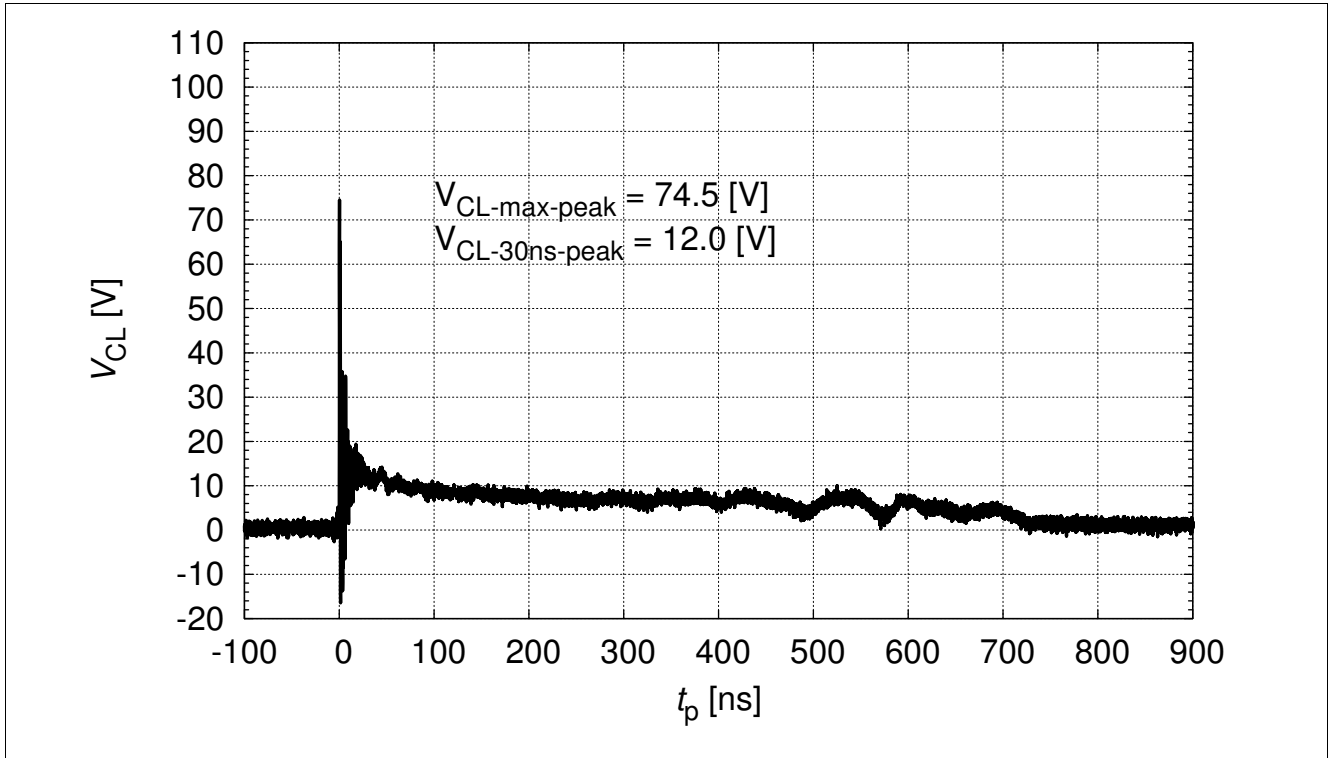


Figure 4-7 IEC61000-4-2 : $V_{CL} = f(t)$, 15 kV positive pulse from pin 1 to pin 2

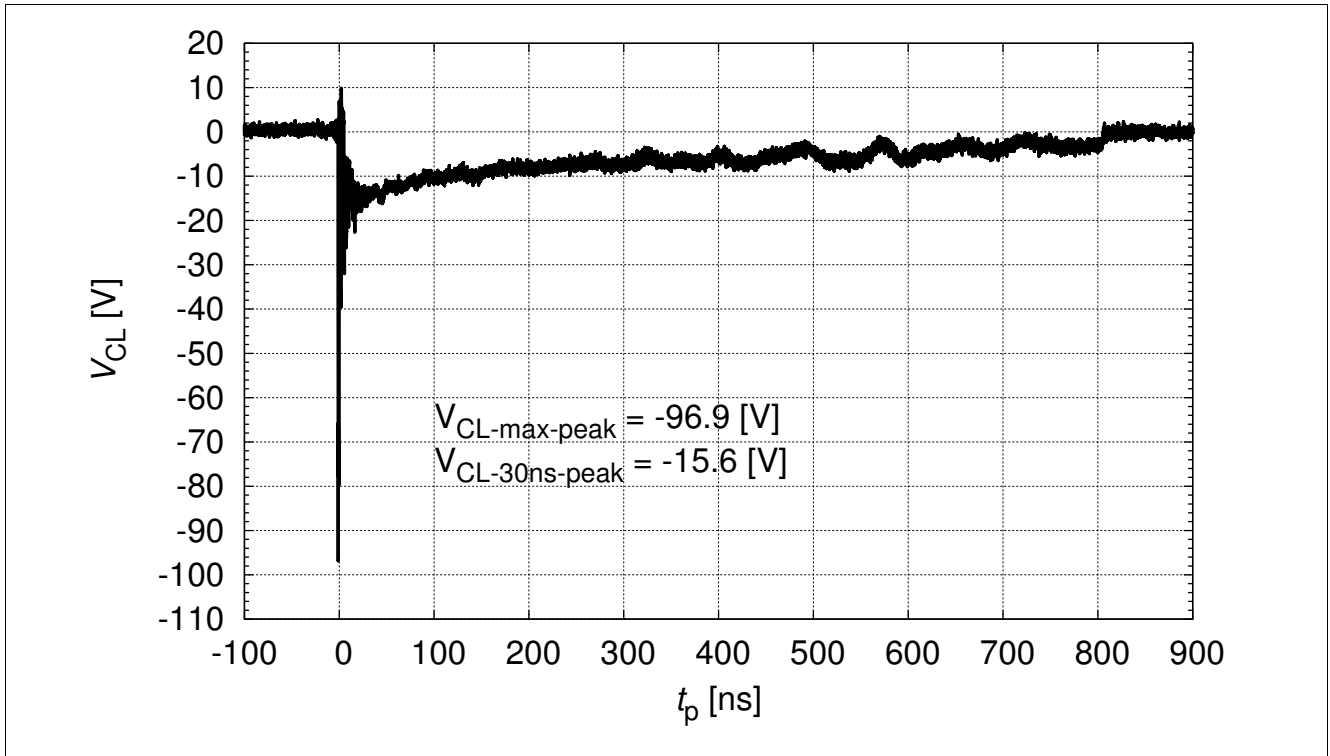


Figure 4-8 IEC61000-4-2 : $V_{CL} = f(t)$, 15 kV negative pulse from pin 1 to pin 2

5 Application Information

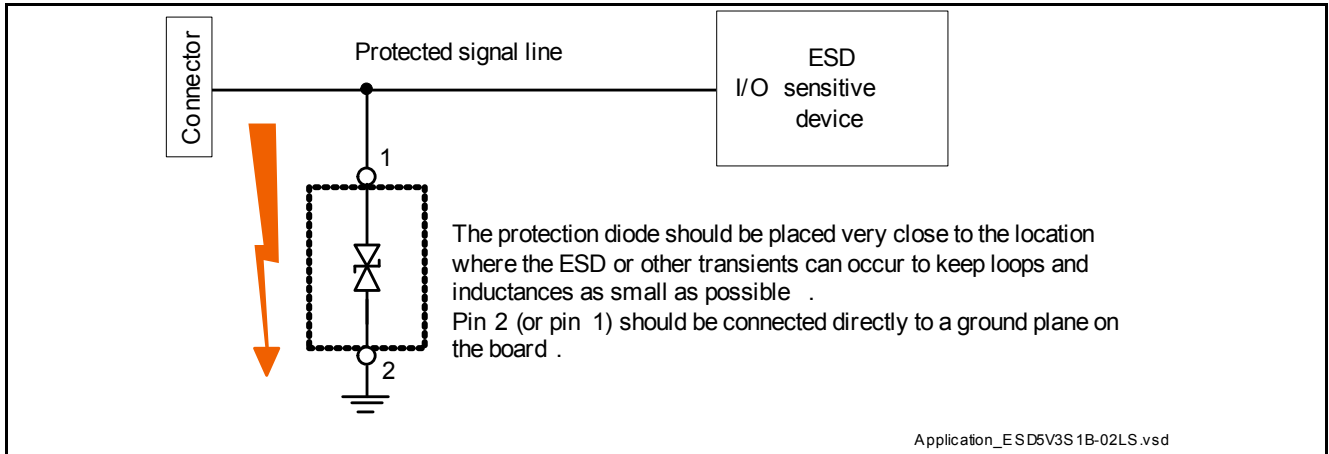


Figure 5-1 Single line, bi-directional ESD / Transient protection

6 Ordering Information Scheme (Examples)

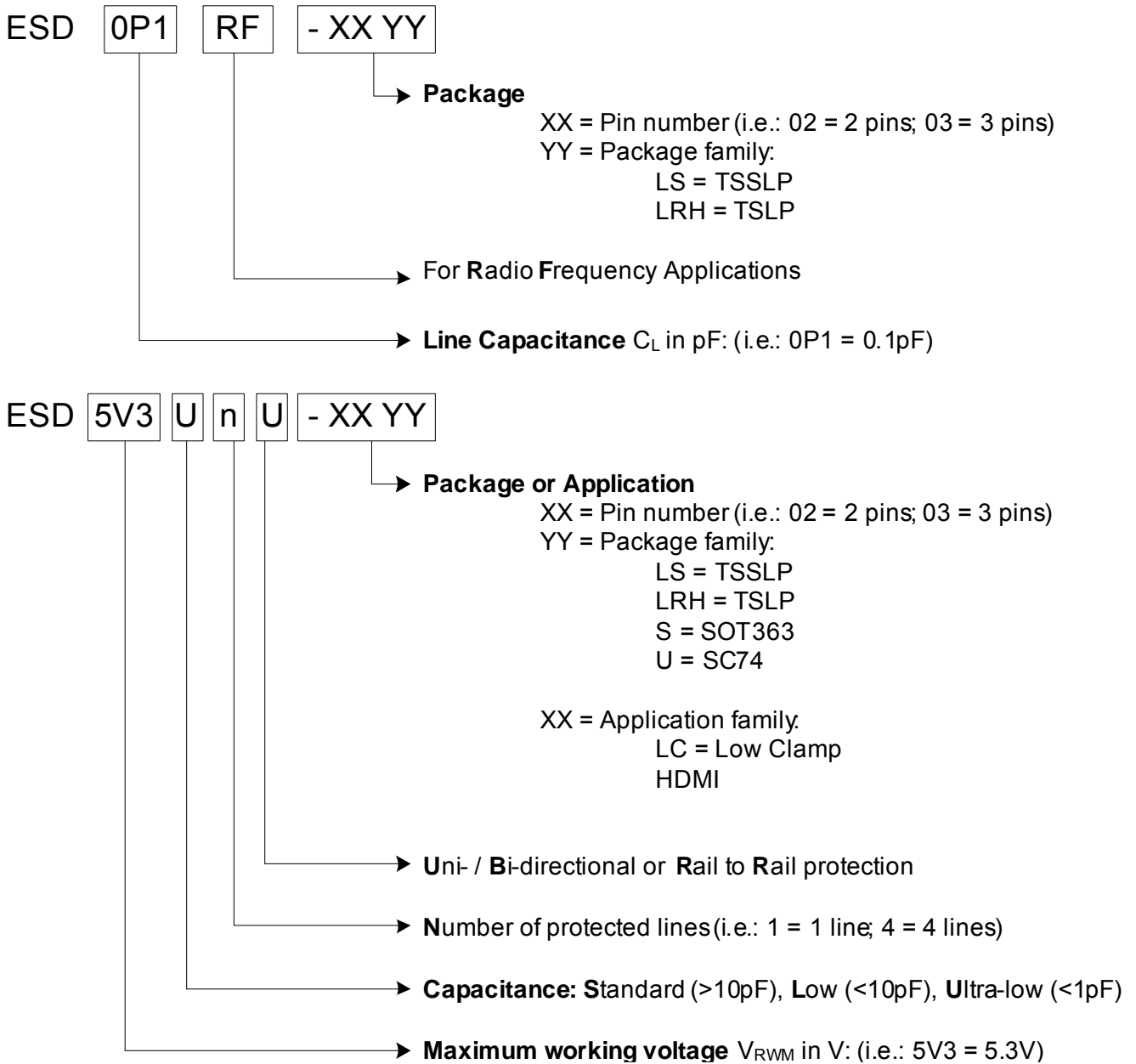


Figure 6-1 Ordering information scheme

7 Package Information

7.1 PG-TSLP-2-17 (mm) [2]

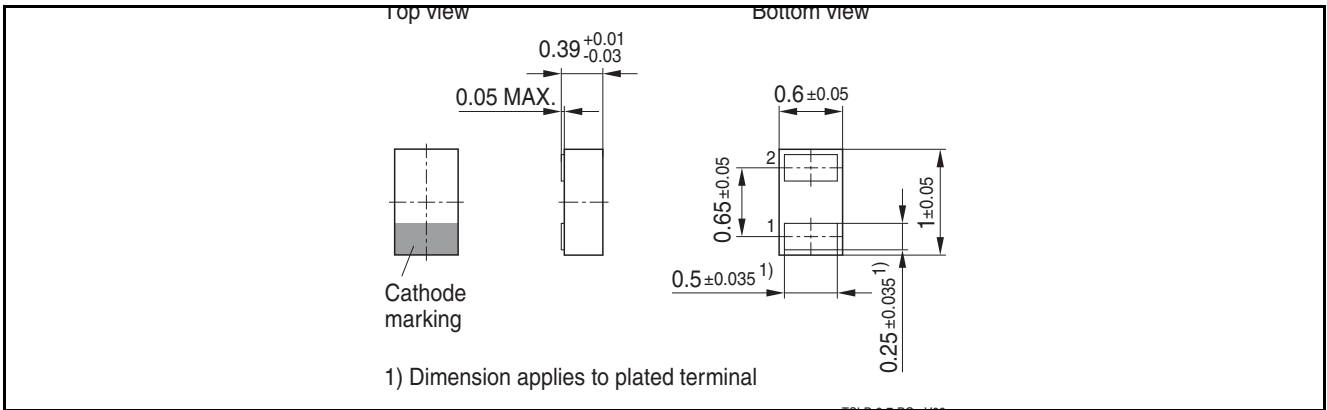


Figure 7-1 PG-TSLP-2-17: Package overview

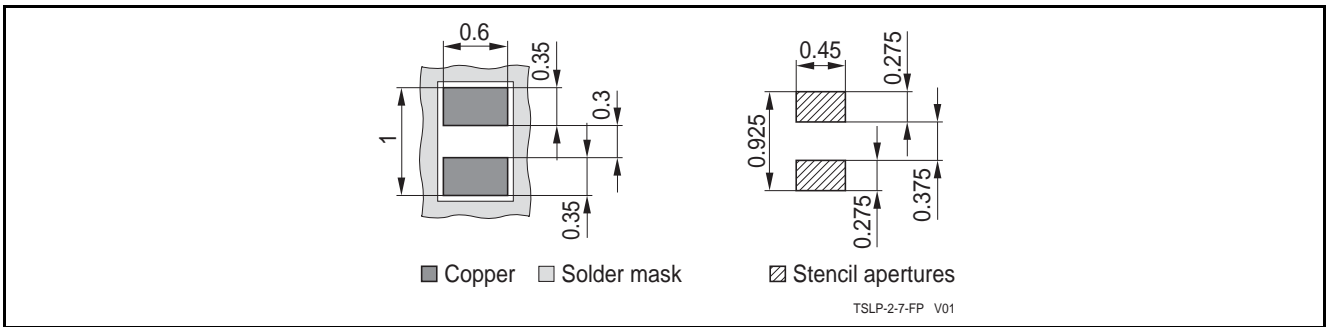


Figure 7-2 PG-TSLP-2-17: Footprint

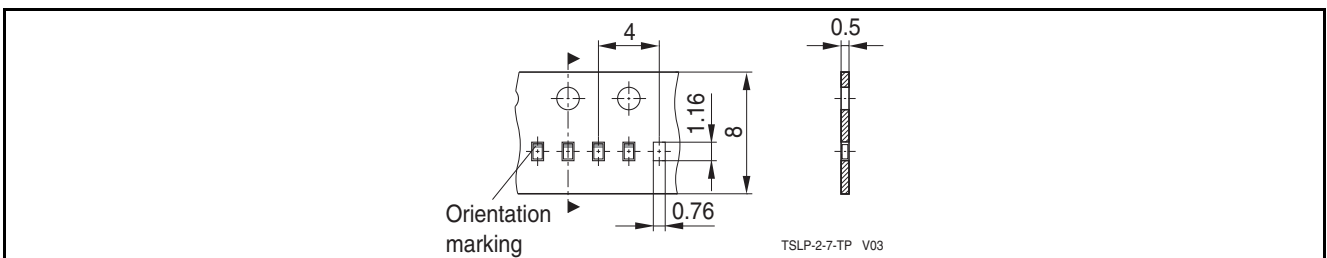


Figure 7-3 PG-TSLP-2-17: Packing

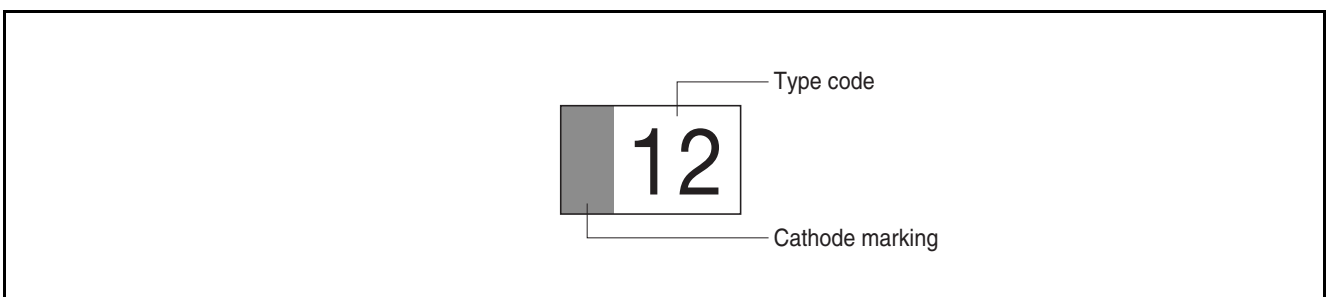


Figure 7-4 PG-TSLP-2-17: Marking (example)

7.2 PG-TSSLP-2-1 (mm) [2]

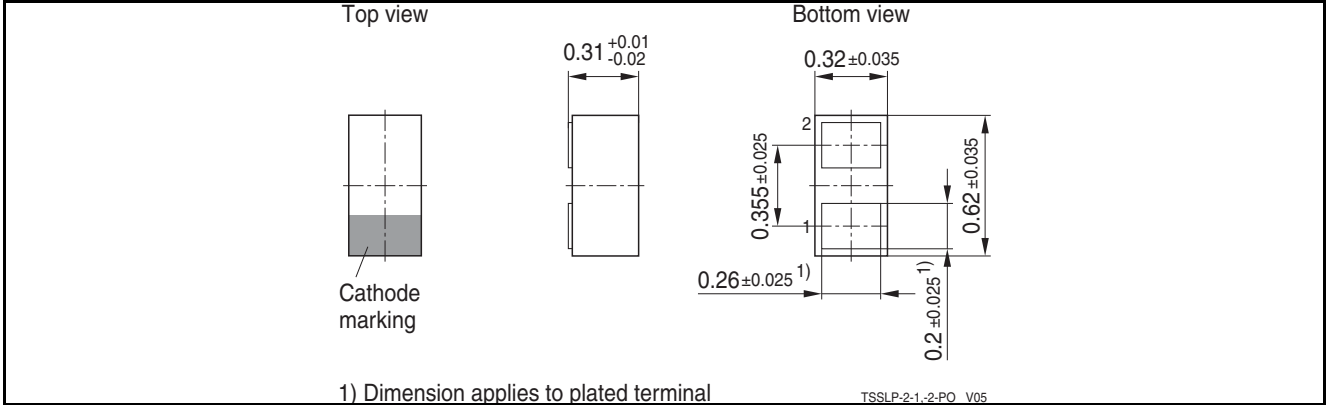


Figure 7-5 PG-TSSLP-2-1: Package overview

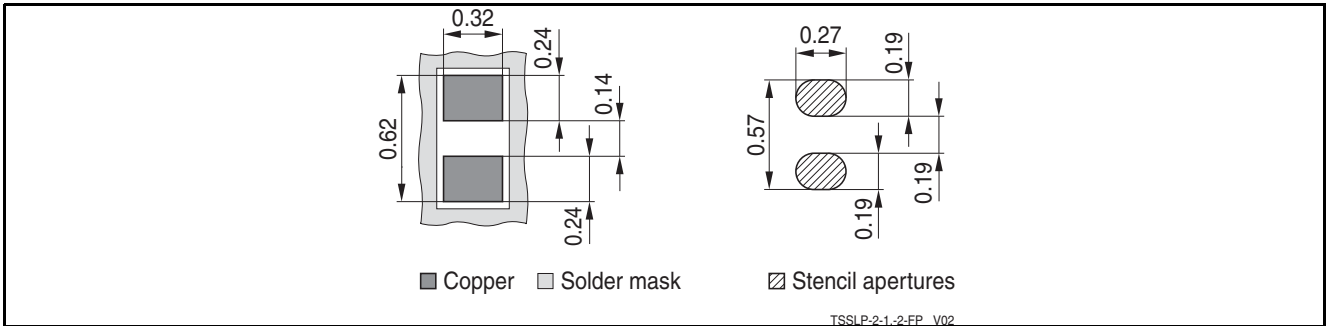


Figure 7-6 PG-TSSLP-2-1: Footprint

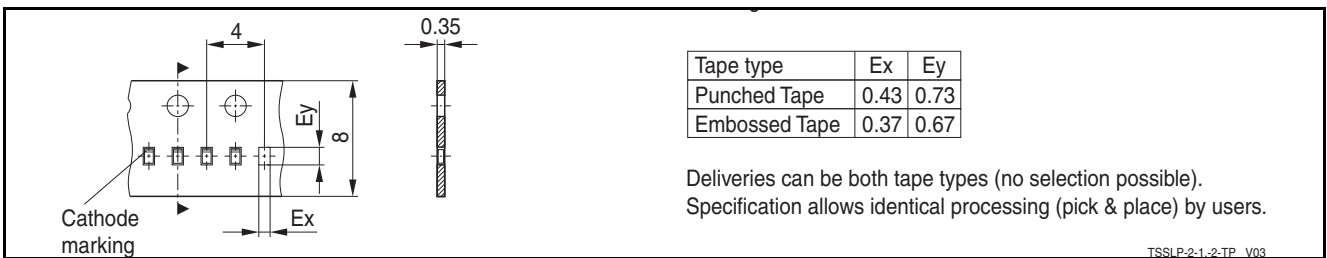


Figure 7-7 PG-TSSLP-2-1: Packing

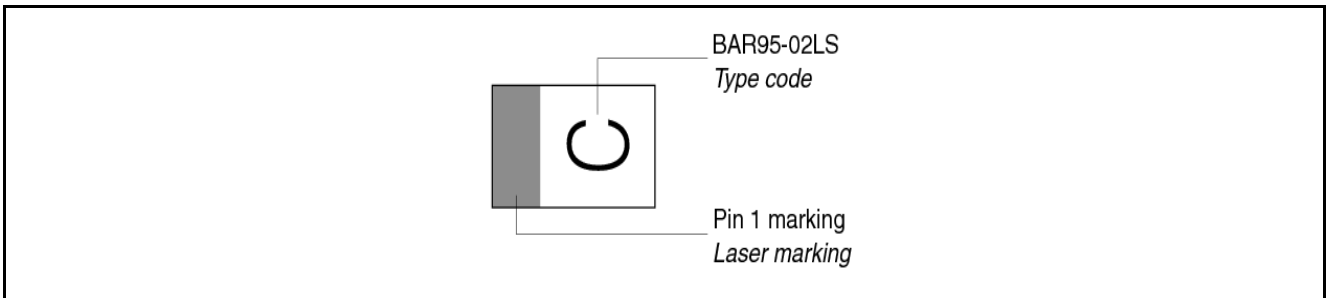


Figure 7-8 PG-TSSLP-2-1: Marking (example)

References

- [1] Infineon AG - **Application Note AN210**: Effective ESD Protection design at System Level Using VF-TLP Characterization Methodology
- [2] Infineon AG - Recommendations for PCB Assembly of Infineon TSLP and TSSLP Packages

Terminology

C_L	Line capacitance
DSC	Digital Still Camera
DVD	Digital Versatile Disc
EFT	Electrical Fast Transient
ESD	Electrostatic Discharge
I_{PP}	Peak pulse current
I_R	Reverse current
LCD	Liquid Crystal Display
MP3	Audio player device based on MPEG Audio Layer III
P_{PK}	Peak pulse power
R_{DYN}	Dynamic resistance
RoHs	Restriction of Hazardous Substance directive
STB	Set-Top-Box
T_A	Ambient temperature
T_{OP}	Operation temperature
t_p	Pulse duration
T_{stg}	Storage temperature
V_{BR}	Breakdown voltage
V_{CL}	Reverse clamping voltage
V_{ESD}	Electrostatic discharge voltage
V_R	Reverse voltage
V_{RWM}	Reverse working voltage maximum

Predefined Names

Name	Initial Cross-Reference
X-GOLD	X-GOLD
XMM	XMM

Definition of “Predefined Names”

Frequently used expressions, such as component names, file names, tools releases, version numbers, proprietary variables and software links, can be used in a similar way as user variables. However, they must be listed in a special table and **not** in the standard file “Variables”.

Correct Usage

Steps:

1. Insert all expressions into the left column of the above table.
2. Insert an initial Cross-Reference into the right column of the same row. The initial Cross-Reference is necessary to ensure that a single ID is used in all your documents using the “Predefined_Names.fm” file (Example: **X-GOLD** has the unique ID = CHDGHJGH).
3. Insert a Cross-Reference (Element “CrossReference”) into your document to the Element Identifier of the “Predefined_Names.fm” file. Set the output format of the Cross-Reference to “Variable” (example: X-GOLD).

Notes

1. All documents in a project (such as XMM) and within a book should use the same file “Predefined Names”. This allows copying content between different documents. For this reason, local versions of “Predefined Names” must not be produced.
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3. This file does not need to be included in your book, but it must be in the fm sub-folder of your document.
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